



AMENDMENTS TO THE CLAIMS

Claims 1-21 (Cancelled)

22. (Currently Amended) The A semiconductor device ~~according to claim 20~~, further comprising:

a semiconductor chip;

at least a first electrode formed on a first major surface of said semiconductor chip;

at least a second electrode formed on a second major surface of said semiconductor chip opposite to said first major surface;

at least a conductive member connecting said first electrode to said second electrode and covering a side surface of said semiconductor chip; and

a conductive line pattern formed on said second major surface and extending from said second electrode.

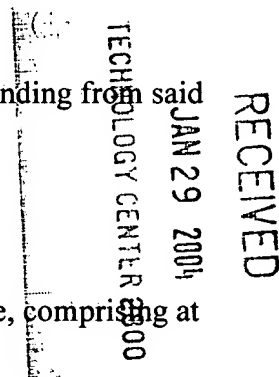
23. (Currently Amended) A composite semiconductor device structure, comprising at least two semiconductor devices ~~as defined in claim 20~~, wherein

each of said semiconductor devices include:

a semiconductor chip;

at least a first electrode formed on a first major surface of said semiconductor chip;

at least a second electrode formed on a second major surface of said semiconductor chip opposite to said first major surface;



at least a conductive member connecting said first electrode to said second electrode and covering a side surface of said semiconductor chip;
said at least two semiconductor devices are stacked on each other, and
a conductive member of a lower one of said semiconductor devices is directly connected to a conductive member of an upper one of said semiconductor devices.

24. (Currently Amended) A composite semiconductor device structure, comprising at least two semiconductor devices ~~as defined in claim 21~~, wherein

each of said semiconductor devices include:
a semiconductor chip;
at least a first electrode formed on a first major surface of said semiconductor chip;
an insulating layer formed on a second major surface of said semiconductor chip opposite to said first major surface;
at least a second electrode formed on said insulating layer;
at least a conductive member connecting said first electrode to said second electrode and covering a side surface of said semiconductor chip;
said at least two semiconductor devices are stacked on each other, and
a conductive member of a lower one of said semiconductor devices is directly connected to a conductive member of an upper one of said semiconductor devices.

25. (Previously Presented) A composite semiconductor device structure, comprising at least two semiconductor devices as defined in claim 22, wherein
said at least two semiconductor devices are stacked on each other, and

a conductive line pattern extending from a first electrode on a first major surface of a lower one of said semiconductor devices is connected via a bump to a conductive line pattern extending from a second electrode on a second major surface of an upper one of said semiconductor devices.

Claim 26 (Cancelled)